ABSTRACT

METHOD FOR DEPOSITION OF CONFORMAL FILMS WITH CATALYSIS ASSISTED LOW TEMPERATURE CVD

A method for depositing a film in a substrate processing system includes arranging a substrate on a pedestal in a processing chamber, heating the substrate to a temperature within a predetermined temperature range, and supplying a gas mixture to the processing chamber for a predetermined period to deposit the film on the substrate, wherein the gas mixture includes a first precursor gas, ammonia gas and diborane gas.

FIG. 1